

|              |         |   |
|--------------|---------|---|
| <b>SANYO</b> | No.715D | DS-446  |
|              |         | Silicon Epitaxial Planar Type<br>Temperature Compensation Use<br><b>Very High-Speed Switching Diode</b> |

**Features**

- Glass sleeve structure
- Power dissipation :  $P = 300\text{mW}$  max.
- Interterminal capacitance :  $C = 3.0\text{pF}$  max.
- Reverse recovery time :  $t_{rr} = 4.0\text{ns}$  max.

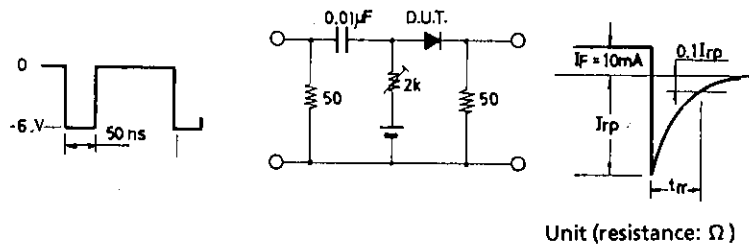
**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$**

|                           |                     |             | unit             |
|---------------------------|---------------------|-------------|------------------|
| Peak Reverse Voltage      | $V_{RM}$            | -105        | V                |
| Reverse Voltage           | $V_R$               | -100        | V                |
| Peak Forward Current      | $I_{FM}$            | 500         | mA               |
| Average Rectified Current | $I_O$               | 200         | mA               |
| Surge Forward Current     | $I_{FSM}$ 1 s pulse | 700         | mA               |
| Power Dissipation         | $P$                 | 300         | mW               |
| Junction Temperature      | $T_j$               | 175         | $^\circ\text{C}$ |
| Storage Temperature       | $T_{stg}$           | -65 to +175 | $^\circ\text{C}$ |

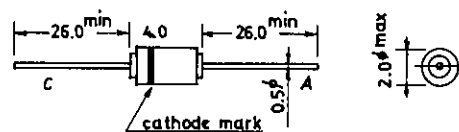
**Electrical Characteristics at  $T_a = 25^\circ\text{C}$**

|                           |          |   | min  | typ | max  | unit          |
|---------------------------|----------|---|------|-----|------|---------------|
| Forward Voltage           | $V_F$    | $I_F = 1.5\text{mA}$                                  | 0.55 |     | 0.65 | V             |
| Reverse Current           | $I_R$    | $V_R = -100\text{V}$                                  |      |     | -0.1 | $\mu\text{A}$ |
| Interterminal Capacitance | $C$      | $V_R = 0\text{V}, f = 1\text{MHz}$                    |      | 1.5 | 3.0  | pF            |
| Reverse Recovery Time     | $t_{rr}$ | $V_R = -6\text{V}, I_F = 10\text{mA}, R_L = 50\Omega$ |      | 2.0 | 4.0  | ns            |

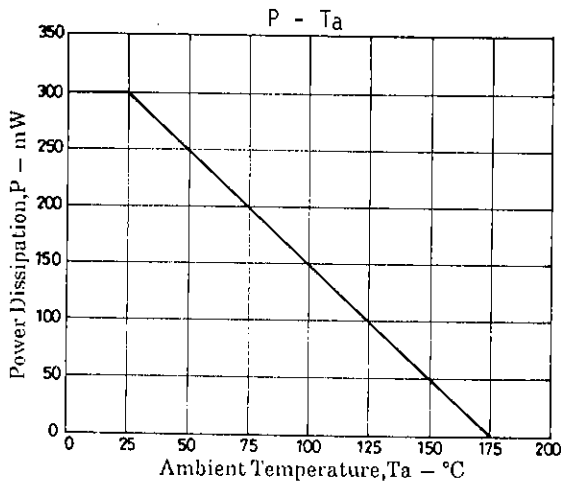
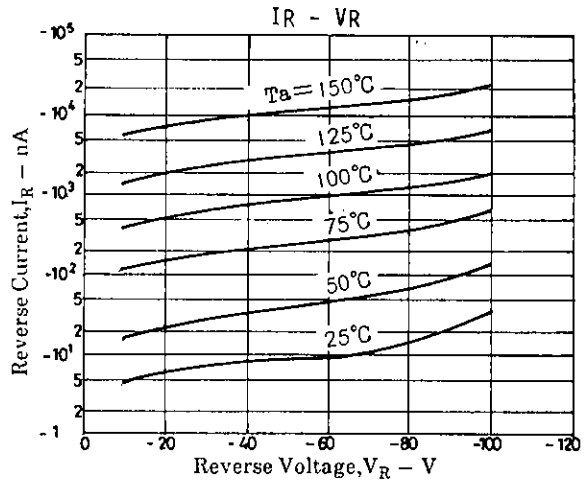
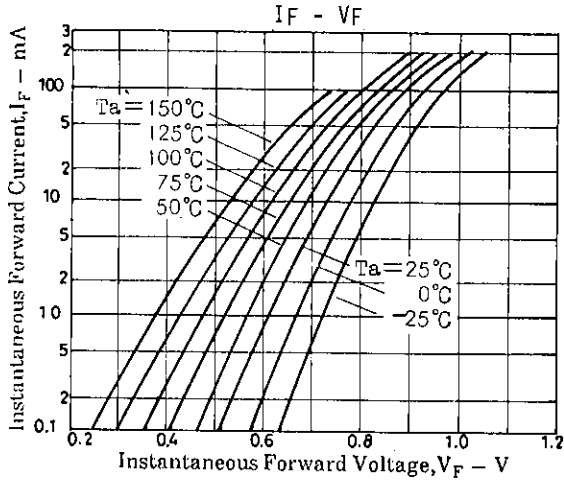
**Reverse Recovery Time Test Circuit**



**Package Dimensions 1080**  
(unit: mm)



C: Cathode  
A: Anode



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